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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	10/678,710
Filing Date	October 3, 2003
First Named Inventor	Lin, *et al.*
Art Unit	TBD
Examiner Name	TBD
Attorney Docket Number	TSM03-0499

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
RMR	1	US-6,465,309 B1	10-15-2002	Xiang, *et al.*	
RMR	2	US-6,475,874 B2	11-05-2002	Xiang, *et al.*	
RMR	3	US-6,518,154 B1	02-11-2003	Buynoski, *et al.*	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3] - Number[4] - Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
RMR	4	TAVEL, B., *et al.*, "Totally Silicided ($CoSi_2$) Polysilicon: A Novel Approach To Very Low-Resistive Gate (~2Ω/□) Without Metal CMP Nor Etching" IEDM (March 2001) pp. 825-828.	
RMR	5	MASZARA, W.P., *et al.*, "Transistors With Dual Work Function Metal Gates By Single Full Silicidation (FUSI) Of Polysilicon," IEDM (February 2002) pp. 367-370.	

Examiner Signature	Rocco N Rocchi	Date Considered	4/1/2004

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